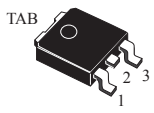
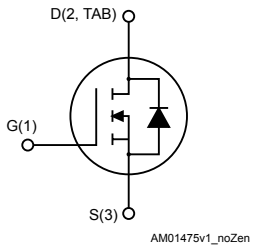
N-channel 60 V, 6.8 mΩ typ., 40 A STripFET™ F7 Power MOSFET in a DPAK package



DPAK



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STD80N6F7	60 V	8.0 mΩ	40 A

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Product status
STD80N6F7

Product summary	
Order code	STD80N6F7
Marking	80N6F7
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	±20	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	40	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	40	A
I_{DM} (2) (1)	Drain current (pulsed)	160	A
P_{TOT}	Total dissipation at T_C = 25 °C	100	W
E_{AS} (3)	Single pulse avalanche energy	60	mJ
dv/dt(4)	Peak diode recovery	4.3	V/ns
T_j	Operating junction temperature range	-55 to 175	°C
T_{stg}	Storage temperature range		

1. *This value is limited by package*
2. *Pulse width limited by safe operating area*
3. *Starting T_j =25 °C, I_{AS}=20 A, V_{DD}=40 V.*
4. *I_{SD} = 20 A, di/dt= 700A/µs, V_{DD} =48 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	50	°C/W
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.5	°C/W

1. *When mounted on FR-4 board of 1 inch², 2oz Cu , t < 10 s*

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 3. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	60			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 60 V			1	µA
I_{GSS}	Gate-body leakage current	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DD} = V_{GS}, I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 20 A		6.8	8.0	mΩ

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 30 V, f = 1 MHz, V_{GS} = 0 V	-	1600	-	pF
C_{oss}	Output capacitance		-	800	-	pF
C_{rss}	Reverse transfer capacitance		-	50	-	pF
Q_g	Total gate charge	V_{DD} = 30 V, I_D = 20 A, V_{GS}= 0 to 10 V (see Figure 13. Test circuit for gate charge behavior)	-	25	-	nC
Q_{gs}	Gate-source charge		-	7.2	-	nC
Q_{gd}	Gate-drain charge		-	8	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}= 30 V, I_D = 20 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	15	-	ns
t_r	Rise time		-	17.6	-	ns
$t_{d(off)}$	Turn-off delay time		-	24.4	-	ns
t_f	Fall time		-	7.8	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD} (1)	Forward on voltage	I_{SD} = 40 A, V_{DD} = 0 V	-		1.2	V
t_{rr}	Reverse recovery time	I_D = 40 A, di/dt = 100 A/µs ,V_{DD} = 48 V (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	39.6		ns
Q_{rr}	Reverse recovery charge		-	36		nC
I_{RRM}	Reverse recovery current		-	1.8		A

1. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

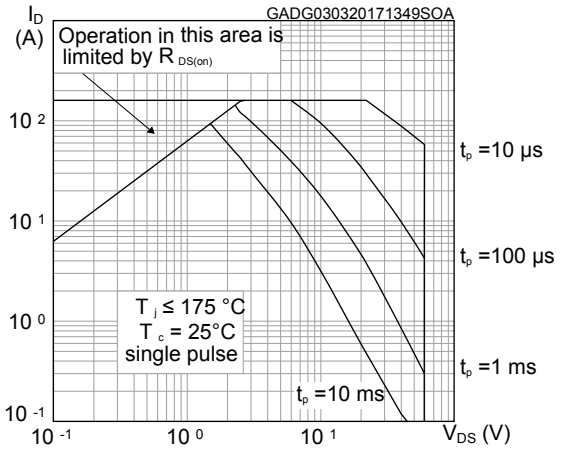


Figure 2. Normalized thermal impedance

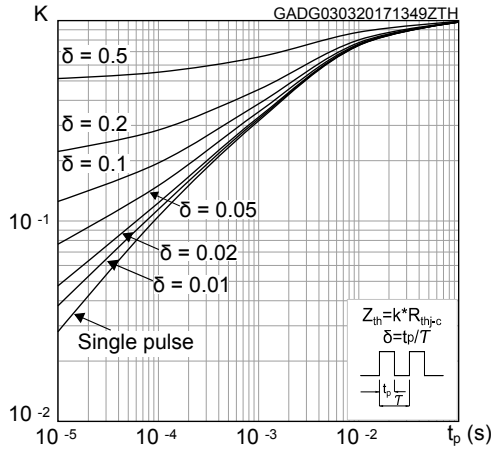


Figure 3. Output characteristics

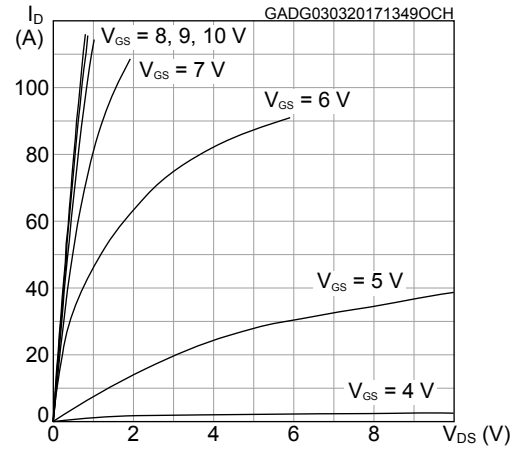


Figure 4. Transfer characteristics

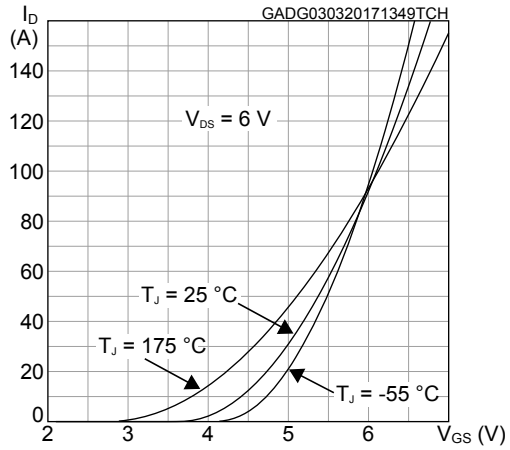


Figure 5. Gate charge vs gate-source voltage

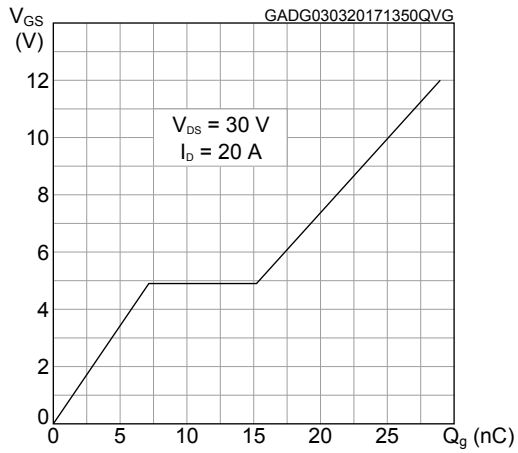


Figure 6. Static drain-source on-resistance

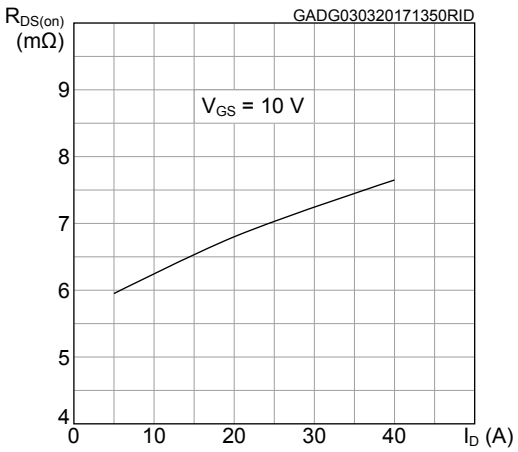


Figure 7. Capacitance variations

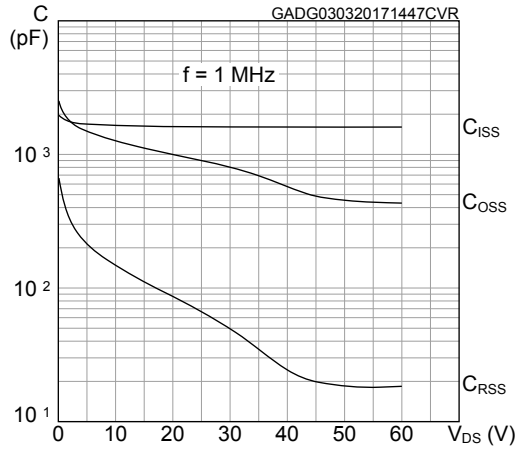


Figure 8. Normalized $V_{GS(th)}$ vs temperature

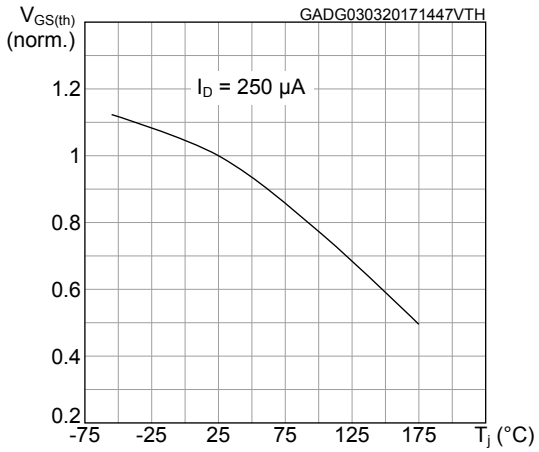


Figure 9. Normalized on-resistance vs temperature

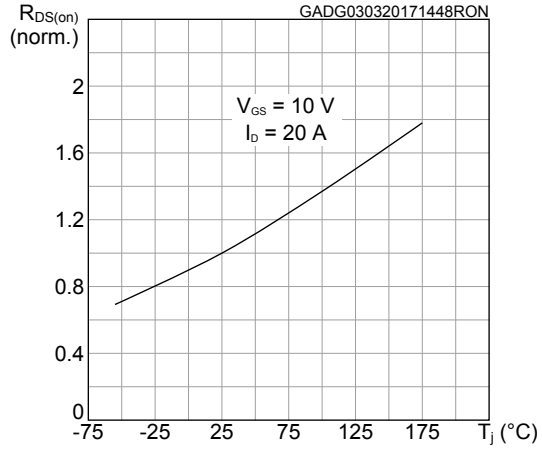


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

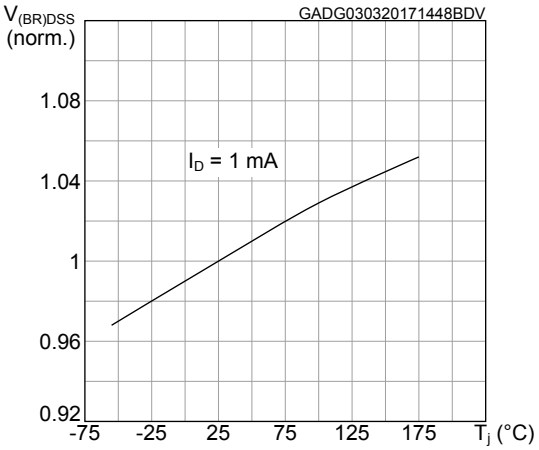
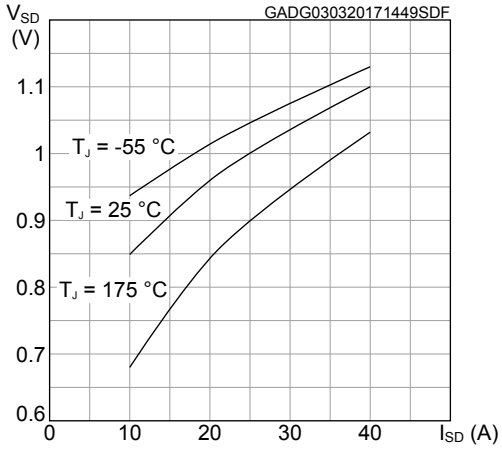


Figure 11. Source-drain diode forward characteristics



3 Test circuits

Figure 12. Test circuit for resistive load switching times

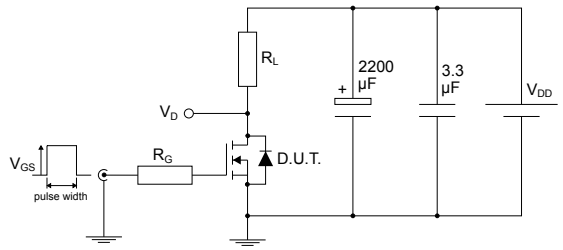


Figure 13. Test circuit for gate charge behavior

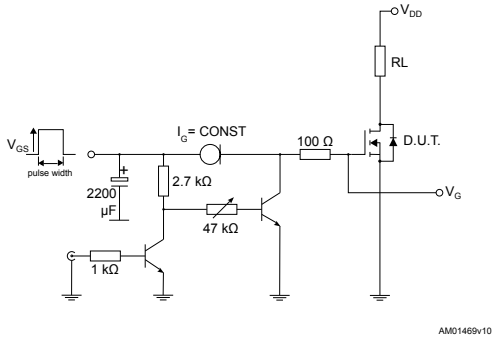


Figure 14. Test circuit for inductive load switching and diode recovery times

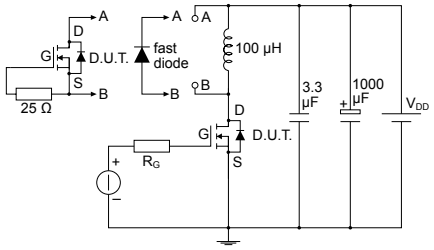


Figure 15. Unclamped inductive load test circuit

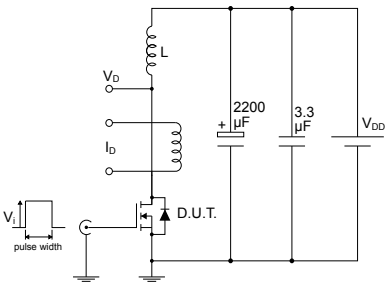


Figure 16. Unclamped inductive waveform

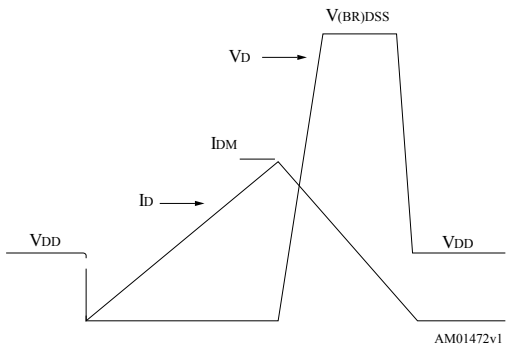
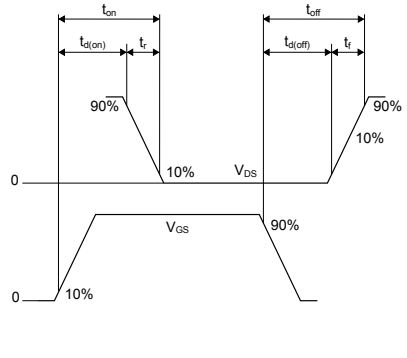


Figure 17. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 18. **DPAK (TO-252) type A2 package outline**

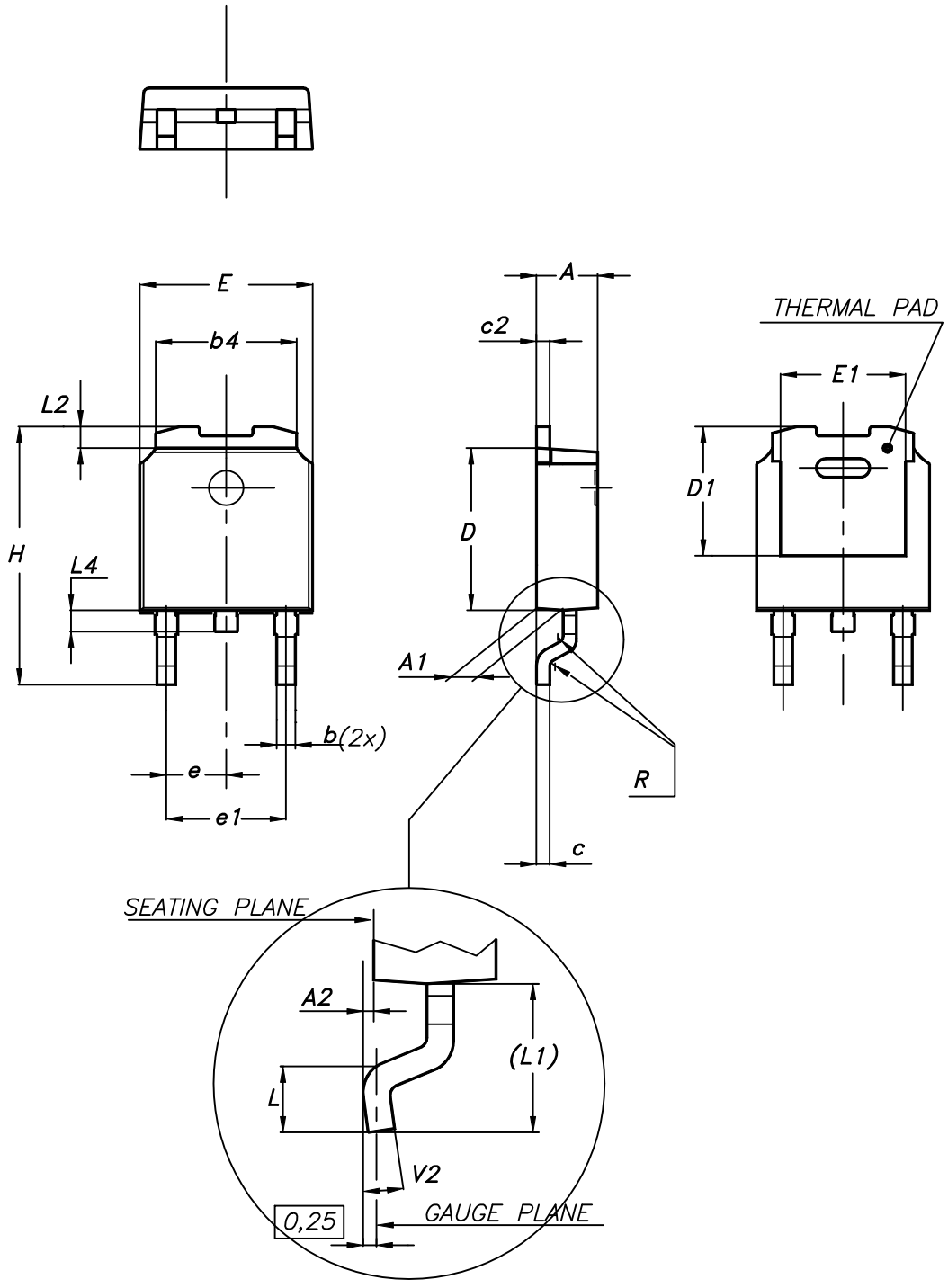


Table 7. **DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C2 package information

Figure 19. **DPAK (TO-252) type C2 package outline**

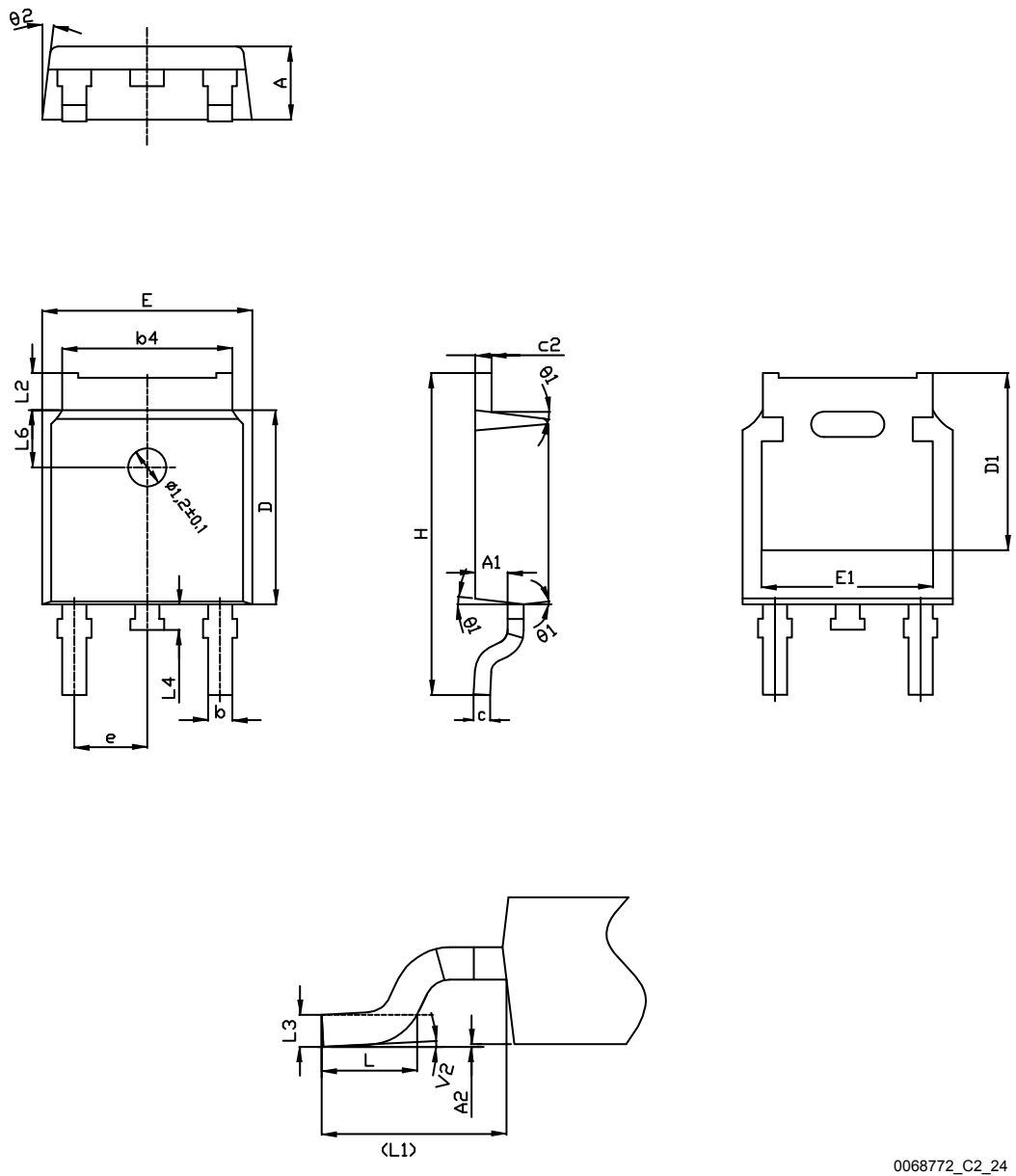


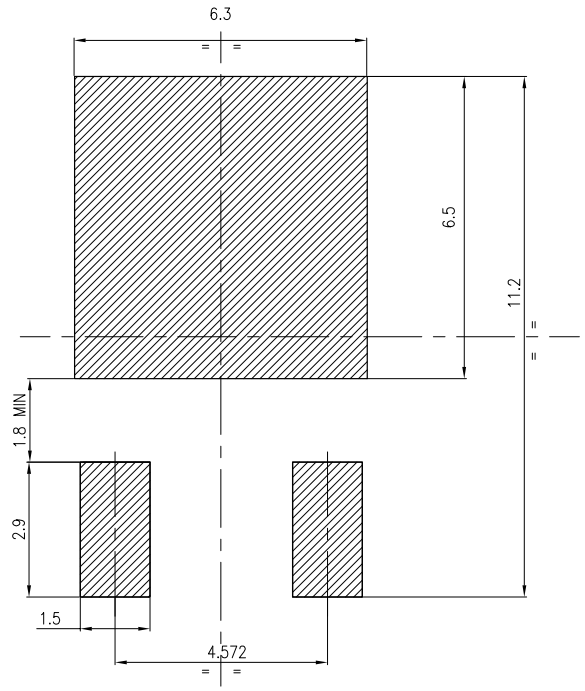
Table 8. **DPAK (TO-252) type C2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46

Dim.	mm		
	Min.	Typ.	Max.
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1		2.90 REF	
L2	0.90		1.25
L3		0.51 BSC	
L4	0.60	0.80	1.00
L6		1.80 BSC	
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.3 DPAK (TO-252) footprint information

Figure 20. DPAK (TO-252) recommended footprint (dimensions are in mm)



Revision history

Table 9. **Document revision history**

Date	Revision	Changes
03-Nov-2016	1	First release
03-Mar-2017	2	Updated *Table 2: "Absolute maximum ratings"* and *Table 5: "Dynamic"*. Added Section 2.1: "*Electrical characteristics (curves)*". Minor text changes.
02-May-2017	3	Updated *Table 2: "Absolute maximum ratings"*.
01-Feb-2018	4	Added DPAK (TO-252) type C package information. Removed maturity status indication from cover page.
12-Feb-2018	5	Modified Section 4 Package information. Minor text changes.

Contents

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